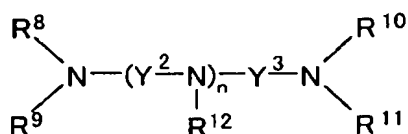


In the Claims

1. (Currently amended) A polishing composition for use in polishing a silicon wafer, the polishing composition ~~characterized by~~ comprising a chelating agent, an alkali compound, silicon dioxide and water, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

2. (Currently Amended) The polishing composition according to claim 1, ~~characterized in that~~ wherein the alkylene group is a lower alkylene group having 1 to 4 carbon atoms.

3. (Currently Amended) The polishing composition according to claim 1 ~~or 2~~, characterized in that the alkyl group is a lower alkyl group having 1 to 4 carbon atoms.

4. (Currently Amended) The polishing composition according to claim 1 ~~any one of claims 1 to 3~~, characterized in that all the alkyl groups have a phosphonic acid group.

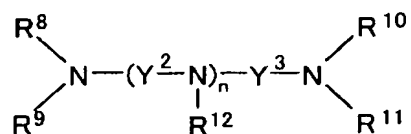
5. (Currently Amended) The polishing composition according to claim 1, ~~characterized in that~~ wherein the chelating agent contains at least one compound selected from ethylenediaminetetraethylenephosphonic acid, ethylenediaminetetramethylenephosphonic acid, diethylenetriaminepentaethylenephosphonic acid, diethylenetriaminepentamethylenephosphonic acid, triethylenetetraminehexaethylenephosphonic acid, triethylenetetraminehexamethylenephosphonic acid,

propanediaminetetraethylenephosphonic acid and
propanediaminetetramethylenephosphonic acid, and ammonium salts, potassium salts,
sodium salts and lithium salts of these acids.

6. (Currently Amended) The polishing composition according to ~~any one of~~
~~claims 1 to 5~~ claim 1, ~~characterized in that~~ wherein the polishing composition has a pH of
from 8 to 12.

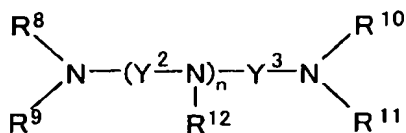
7. (Currently Amended) The polishing composition according to ~~any one of~~
~~claims 1 to 6~~ claim 1, ~~characterized in that~~ wherein n in the chemical formula is an
integer of 0 to 2.

8. (Currently Amended) A process for polishing a silicon wafer, the process
~~characterized by~~ comprising:
preparing a polishing composition and
polishing the surface of the silicon wafer by using the polishing composition,
wherein the polishing composition includes a chelating agent, an alkali
compound, silicon dioxide and water, wherein the chelating agent is an acid represented
by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an
alkylene group, n is an integer of 0 to 4, each of 4+n substituents represented by R⁸ to R¹²
is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

9. (Currently Amended) A rinsing composition for use in rinsing a silicon wafer,
the rinsing composition ~~characterized by~~ comprising a chelating agent, an alkali
compound and water, wherein the chelating agent is an acid represented by the following
chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

10. (Currently Amended) The rinsing composition according to claim 9, ~~characterized in that~~ wherein the alkylene group is a lower alkylene group having 1 to 4 carbon atoms.

11. (Currently Amended) The rinsing composition according to claim 9 ~~or 10, characterized in that~~ wherein the alkyl group is a lower alkyl group having 1 to 4 carbon atoms.

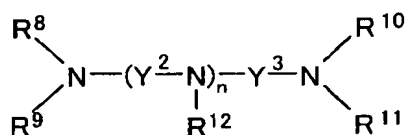
12. (Currently Amended) The rinsing composition according to ~~any one of claims 9 to 11~~ claim 9, characterized in that wherein all the alkyl groups have a phosphonic acid group.

13. (Currently Amended) The rinsing composition according to claim 9, ~~characterized in that~~ wherein the chelating agent contains at least one compound selected from ethylenediaminetetraethylenephosphonic acid, ethylenediaminetetramethylenephosphonic acid, diethylenetriaminepentaethylenephosphonic acid, diethylenetriaminepentamethylenephosphonic acid, triethylenetetraminehexaethylenephosphonic acid, triethylenetetraminehexamethylenephosphonic acid, propanediaminetetraethylenephosphonic acid and propanediaminetetramethylenephosphonic acid, and ammonium salts, potassium salts, sodium salts and lithium salts of these acids.

14. (Currently Amended) The rinsing composition according to ~~any one of claims 9 to 13~~ claim 9, ~~characterized in that~~ wherein the rinsing composition has a pH of from 8 to 12.

15. (Currently Amended) The rinsing composition according to ~~any one of claims 9 to 14~~ claim 9, ~~characterized in that~~ wherein n in the chemical formula is an integer of 0 to 2.

16. (Currently Amended) A process for rinsing a silicon wafer, the process ~~characterized by~~ comprising:
preparing a rinsing composition and
rinsing the surface of the silicon wafer by using the rinsing composition,
wherein the rinsing composition includes a chelating agent, an alkali compound and water, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.